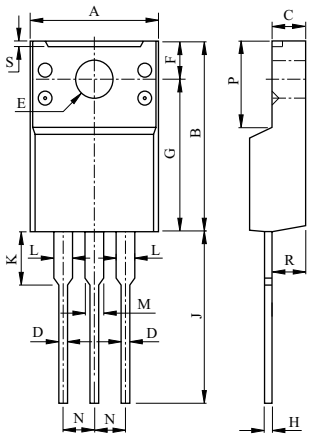
KTD2066

EPITAXIAL PLANAR NPN TRANSISTOR

HIGH CURRENT SWITCHING APPLICATION.
LAMP SOLENOID DRIVER APPLICATION.

FEATURES

- High DC Current Gain
  : h_{FE}=500 ~ 1500(I_C=1A).
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$=0.35V(Max.) (I_C=3A).



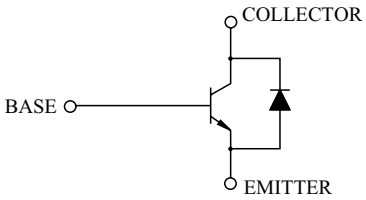
DIM	MILLIMETERS
A	10.0±0.3
B	15.0±0.3
C	2.70±0.3
D	0.76+0.09/-0.05
E	Φ3.2±0.2
F	3.0±0.3
G	12.0±0.3
H	0.5+0.1/-0.05
J	13.6±0.5
K	3.7±0.2
L	1.2+0.25/-0.1
M	1.5+0.25/-0.1
N	2.54±0.1
P	6.8±0.1
Q	4.5±0.2
R	2.6±0.2
S	0.5 Typ

TO-220IS

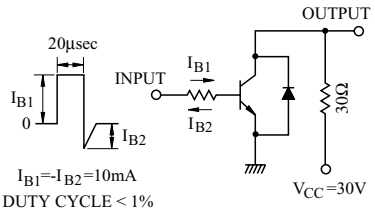
MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	100	V
Collector-Emitter Voltage		V_{CEO}	80	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	5	A
	Pulse	I_{CP}	8	
Base Current		I_B	1	A
Collector Power Dissipation	Ta=25℃	P_C	2	W
	Tc=25℃		30	
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 ~ 150	℃

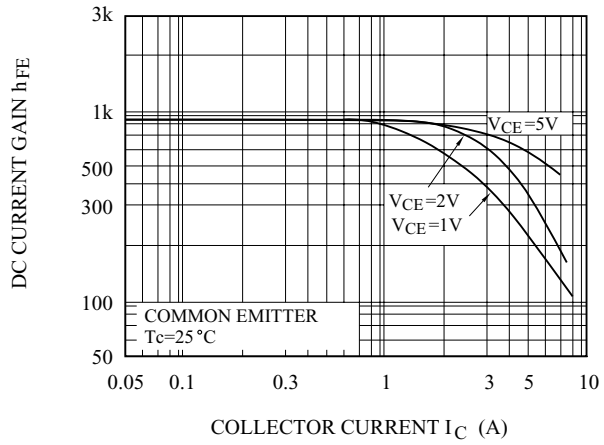
EQUIVALENT CIRCUIT



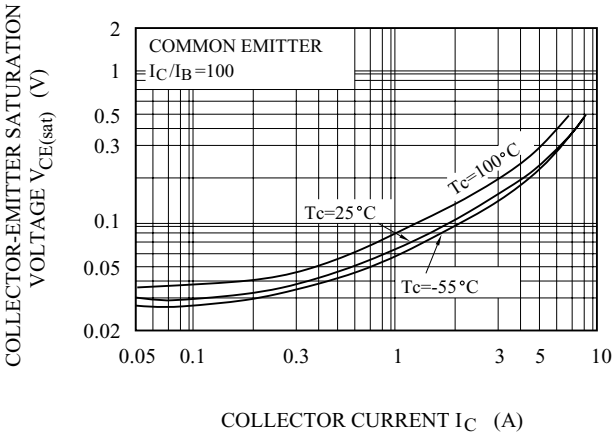
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=80V, I_E=0	-	-	10	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=7V, I_C=0	-	-	10	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=50mA, I_B=0	80	-	-	V
DC Current Gain		h_{FE}(1)	V_{CE}=1V, I_C=1A	500	-	1500	
		h_{FE}(2)	V_{CE}=1V, I_C=5A	150	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=3A, I_B=0.03A	-	-	0.35	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C=3A, I_B=0.03A	-	-	1.2	V
Collector-Emitter Forward Voltage		V_{ECF}	I_E=3A, I_B=0	-	-	2.5	V
Transition Frequency		f_T	V_{CE}=5V, I_C=1A	-	130	-	MHz
Collector Output Capacitance		C_{ob}	V_{CE}=10V, I_E=0, f=1MHz	-	110	-	pF
Switching Time	Turn-on Time	t_{on}		-	0.6	-	μS
	Storage Time	T_{stg}		-	3.0	-	
	Fall Time	t_f		-	0.8	-	

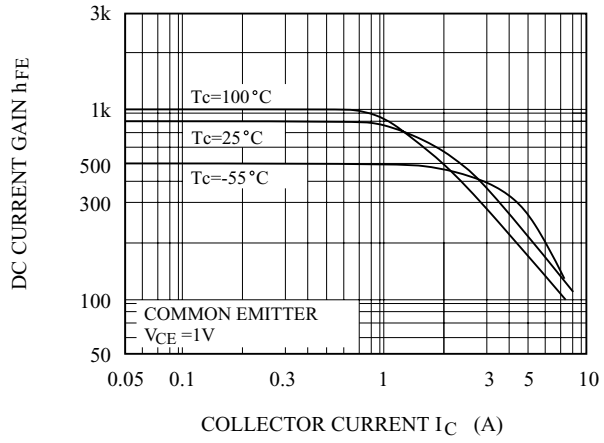
h_{FE} - I_C



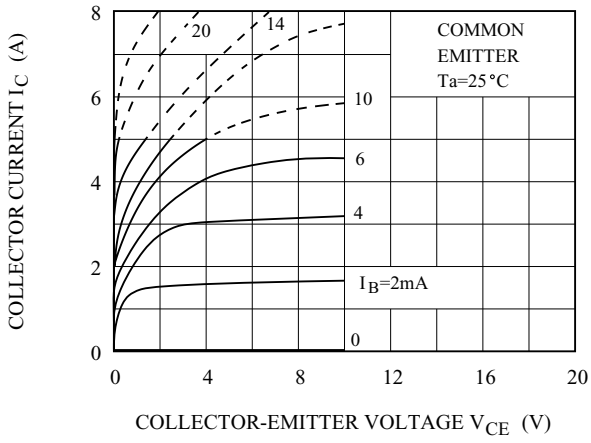
$V_{CE(sat)}$ - I_C



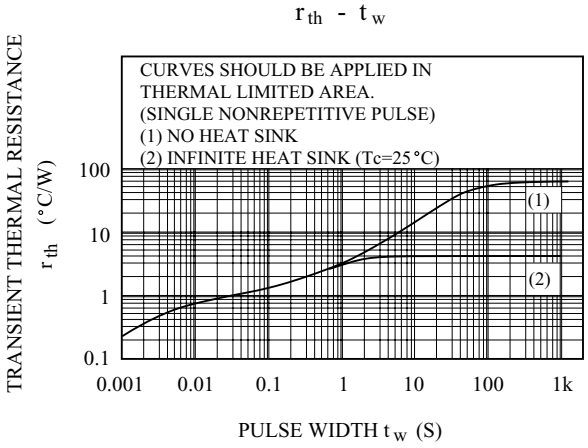
h_{FE} - I_C



I_C - V_{CE}



r_{th} - t_w



SAFE OPERATING AREA